ABSTRACT OF THE DISCLOSURE

A magnetic random access memory includes memory cells each including a TMR element and a selection element, and a read circuit which reads storage information from the TMR element by applying read voltage to a selected one of the memory cells and causing a current to flow through the TMR element via the selection element. The read circuit includes a voltage setting section used to apply voltage which makes a resistance variation rate of the TMR element substantially equal to half a resistance variation rate thereof obtained when 0 V is applied across the TMR element to the TMR element at the information read time.